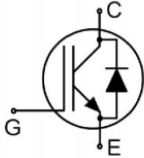


●Features

- Low Gate Charge
- Low Power Loss & High Efficiency
- Guard Ring & Environmental Protection
- High Temperature Application
- Green Molding Compound

	$V_{CES}: 650V$ $I_C: 50A$ $V_{CE(SAT)}: 1.8V$
	■RoHS COMPLIANT TO-247

●Application

- DC-DC Inverters
- UPS
- Industrial Heating

●Ordering Information:

Part Number	LHG50T65T2HD
Package	TO-247
Basic Ordering Unit (pcs)	330
Normal Package Material Ordering Code	LHG50T65T2HD-TO247-TU
Halogen Free Ordering Code	LHG50T65T2HD-TO247-TU-HF

●Absolute Maximum Ratings (Ta=25℃)

Symbol	Parameter	Rating	Unit
Common Ratings (Ta=25℃ Unless Otherwise Noted)			
V _{CES}	Collector- Emitter Voltage (MIN.)	650	V
V _{GES}	Gate-Emitter Voltage	±20	
I _C	Continuous Collector Current	T _C = 25℃	A
		T _C = 100℃	
I _{CM}	Collector Current Continuous (Note 1.)	150.0	A
-	Turn-off Safe Area	150.0	A
P _D	Maximum Power Dissipation (T _C =25℃)	416	W
T _J	Maximum Junction Temperature	-50 to 150	℃
T _{STG}	Storage Temperature Range	-50 to 150	℃
T _L	Maximum Lead Temperature for Soldering Purposes	275	℃

Notes : ¹⁾ Collector current limited by maximum junction temperature.

● Thermal Resistance

Symbol	Parameter	Values		Unit
		Typ.	Max.	
R _{thJC}	Thermal Resistance, Junction - Case	-	0.46	℃/W
R _{thJA}	Thermal Resistance, Junction - Ambient	-	56	℃/W

● Electrical Characteristics (T_J=25℃ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	Values			Unit
			Min.	Typ.	Max.	
Off Characteristics						
BV _{CES}	Collector-Emitter Breakdown Voltage	V _{GS} =0V, I _C =250uA	650	-	-	V
I _{CES}	Zero Gate Voltage Drain Current	V _{CE} = 600V, V _{GE} = 0V, T _C =25°C	-	-	1.0	mA
I _{GESF}	Gate-body Leakage Current (Forward)	V _{CE} =0V, V _{GE} =20V	-	-	250	nA
I _{GESR}	Gate-body Leakage Current (Reverse)	V _{CE} =0V, V _{GE} =-20V	-	-	-250	nA
ΔBV _{CES} /ΔT _J	Breakdown Voltage Temperature Coefficient.	I _C =1mA, Reference to 25°C	-	0.6	-	V/°C

• Electrical Characteristics ($T_J=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	Values			Unit
			Min.	Typ.	Max.	
On Characteristics						
$V_{GE(th)}$	Gate Threshold Voltage	$V_{CE} = V_{GE}$, $I_C=1mA$	4.0	5.36	7.0	V
$V_{CE(SAT)}$	Collector- Emitter Saturation Voltage	$V_{GE}=15V$, $I_C=50A$ $T_C = 25^{\circ}C$	-	1.8	2.4	V

• Electrical Characteristics ($T_J=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	Values			Unit
			Min.	Typ.	Max.	
Switching Characteristics						
C _{ies}	Input Capacitance	V _{CE} =30V, V _{GE} =0V, Frequency=1.0MHz	-	7719	-	pF
C _{oes}	Output Capacitance		-	189	-	
C _{res}	Reverse Transfer Capacitance		-	123	-	
t _{d(ON)}	Turn-on Delay Time	V _{CE} = 400V, I _C = 50A, R _G = 10Ω V _{GE} = 15V T _C =25°C	-	94	-	nS
t _r	Turn-on Rise Time		-	92	-	
t _{d(OFF)}	Turn-off Delay Time		-	335	-	
t _f	Turn-off Fall Time		-	60	-	
E _{on}	Turn-on Energy		-	3.53	-	mJ
E _{off}	Turn-off Energy	-	1.40	-		
E _{total}	Total Switching Energy	-	4.93	-		
Q _g	Total Gate Charge	V _{CE} =400V, V _{GE} =15V, I _C =50A	-	303	-	nC
Q _{ge}	Gate to Emitter Charge		-	77	-	
Q _{gc}	Gate to Collector Charge		-	128	-	
Anti-Parallel Diode Characteristics and Maximum Ratings						
V _F	Emitter-Collector Diode Forward Voltage	VGS=0V, Is=25.0A	-	1.65	2.0	V
t _{rr}	Reverse Recovery Time	I _S =25A, V _{GE} =0V, VR=400V dl _F /dt=100A/μs (Note 4)	-	80	-	nS
Q _{rr}	Reverse Recovery Charge		-	240	-	nC
I _{RRM}	Diode Reverse Recovery Current		-	6	-	A

Note 1 : Pulse width limited by maximum junction temperature.

Note 2 : Allowed number of short circuits: < 1000 Time between short circuit: >1s.

Note 3 : Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

Note 4 : Essentially independent of operating temperature.

● Electrical Characteristic Curves

Fig. 1 Typical Output Characteristics

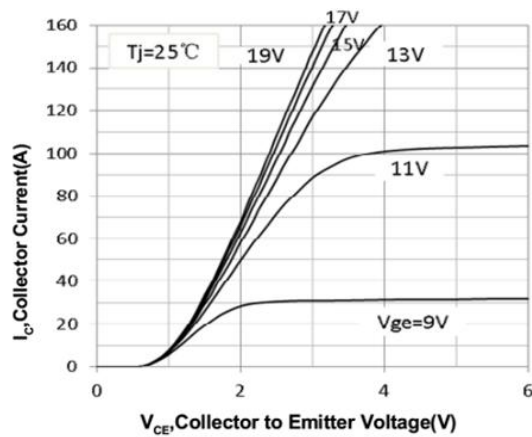


Fig. 2 Typical Output Characteristic

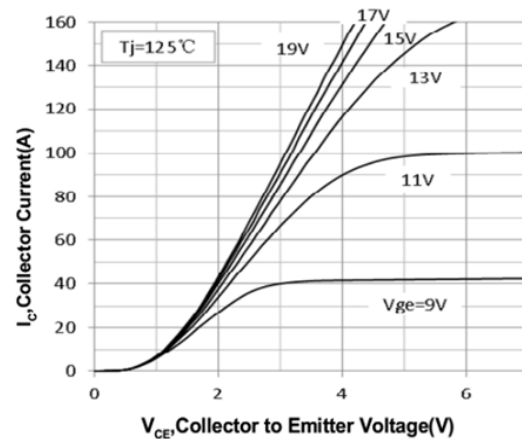


Fig. 3 $V_{CE(SAT)}$ vs. I_C Characteristics

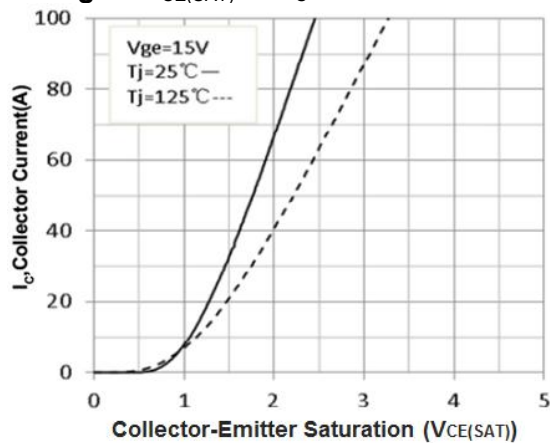


Fig. 4 $V_{CE(SAT)}$ vs. T_C

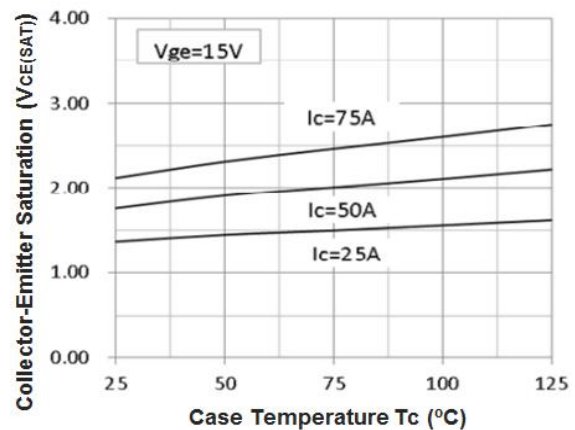


Fig. 5 Capacitance Characteristics

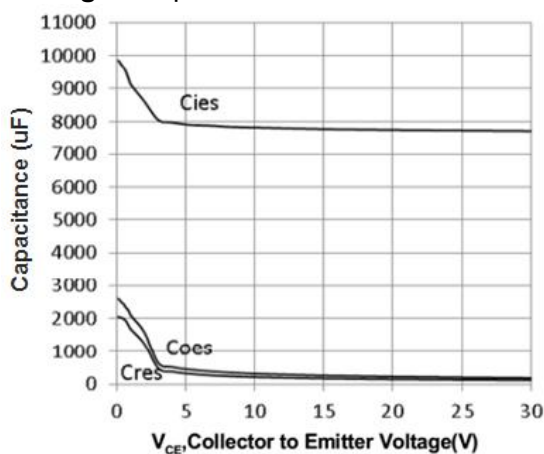
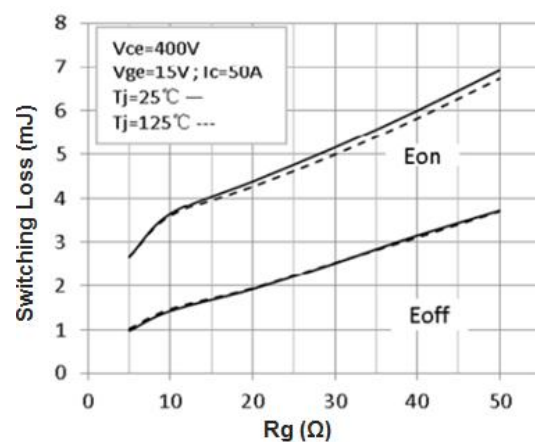


Fig. 6 Switching Energy Loss Characteristics



● **Electrical Characteristic Curves**

Fig. 7 R_g vs. Switching Time

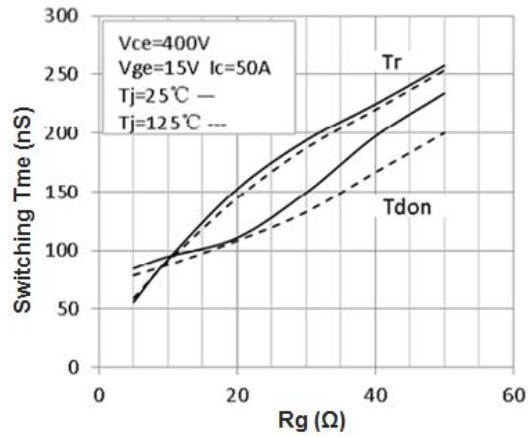


Fig. 8 R_g vs. Switching Time

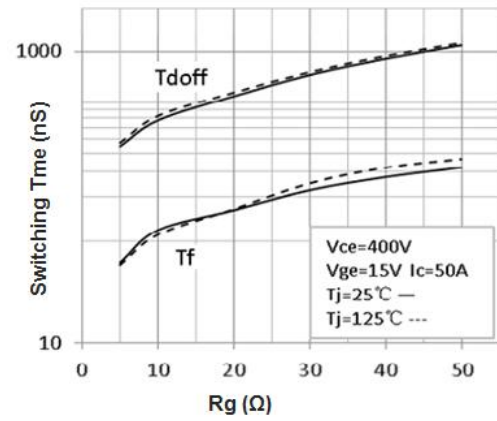


Fig. 9 T_c vs. Switching Time

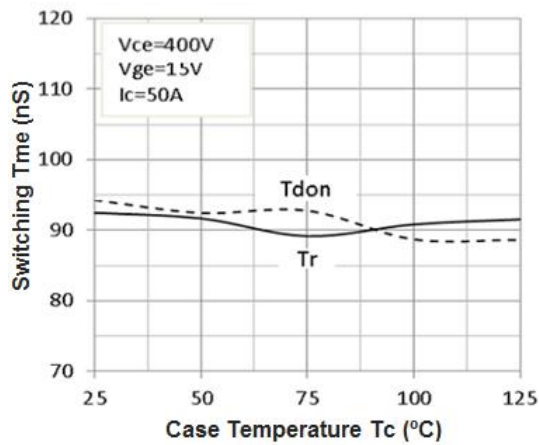


Fig. 10 T_c vs. Switching Time

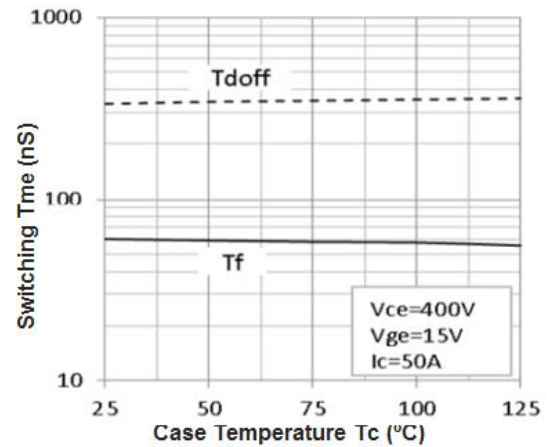


Fig. 11 T_c vs. Switching Loss

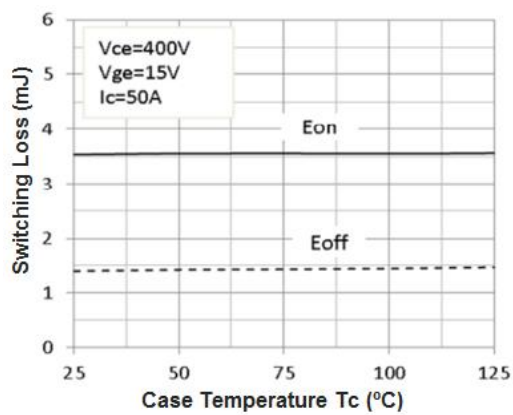
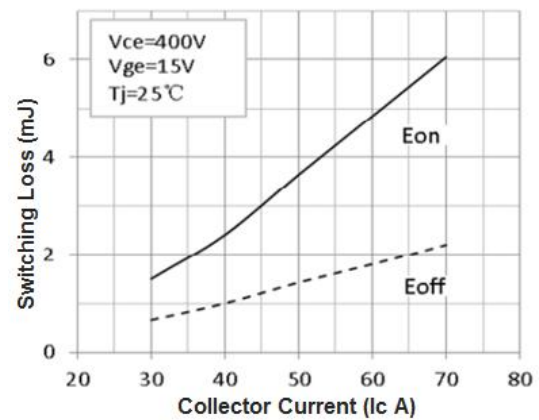


Fig. 12 I_c vs. Switching Loss



● **Electrical Characteristic Curves**

Fig. 13 I_C vs. Switching Time

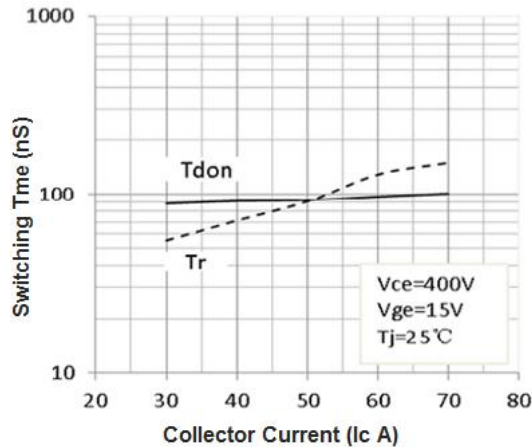


Fig. 14 I_C vs. Switching Time

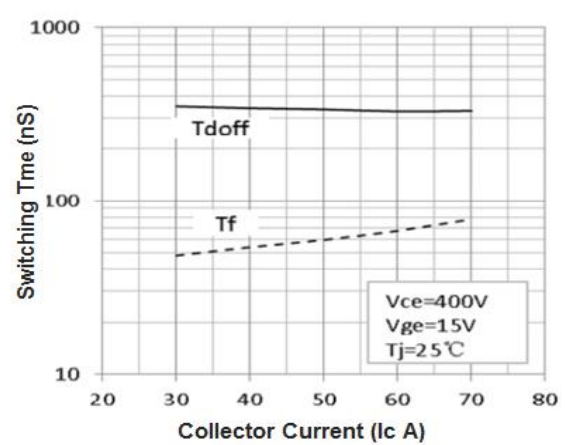


Fig. 14 Reverse Diode Characteristics

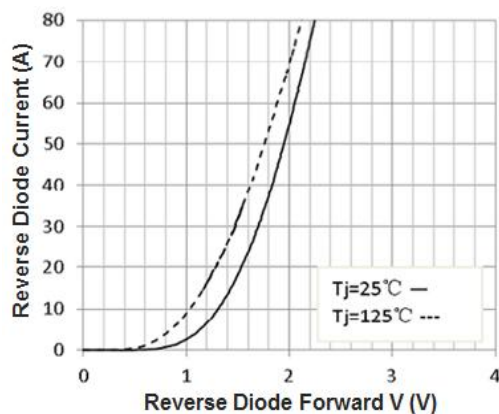


Fig. 15 T_C vs. I_C Current (A)

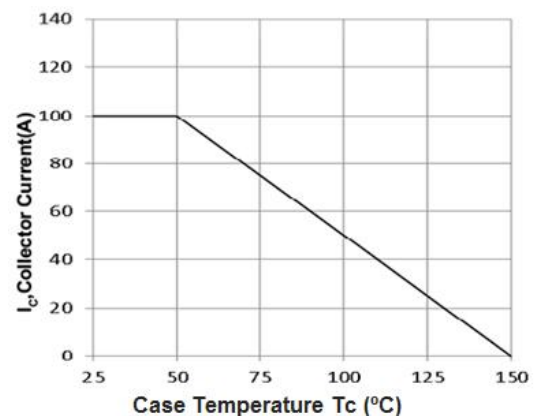


Fig. 17 Safety Area

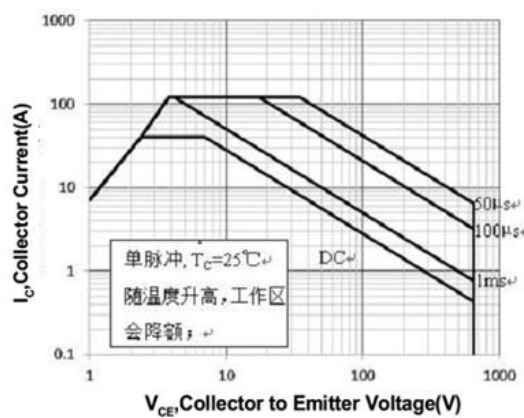
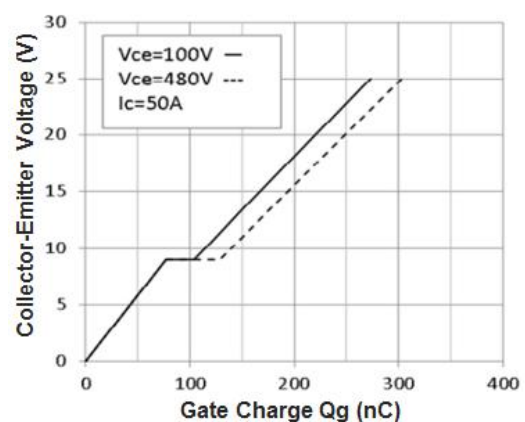
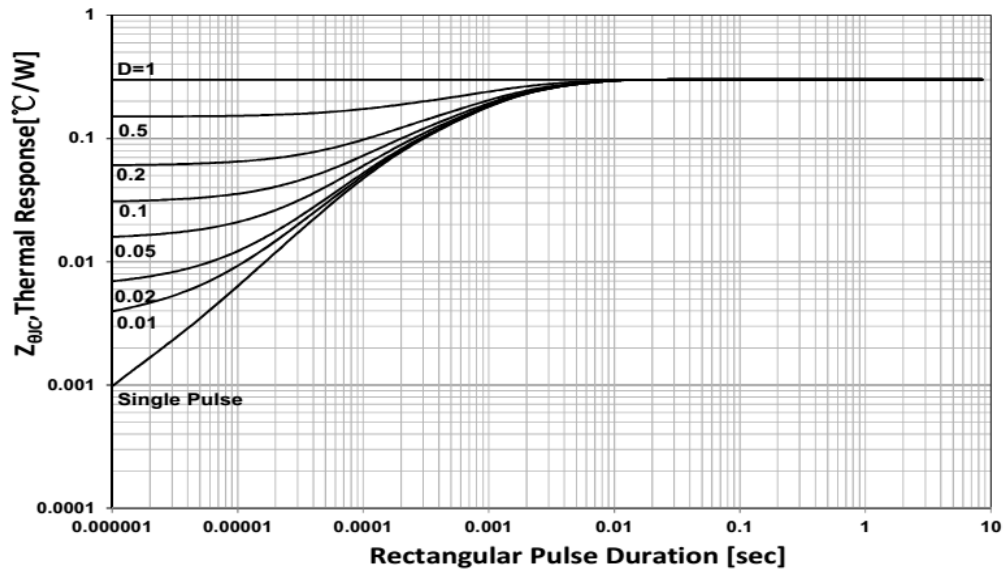


Fig. 18 Gate Charge Characteristics



- Electrical Characteristic Curves

Fig. 19 Transient Thermal Impedance for IGBT



●Dimensions (TO-247)

UNIT:mm

SYMBOL	min	max	SYMBOL	min	max
A	15.60	16.00	G2	1.95	2.25
B	20.80	21.20	N	5.25	5.65
C	4.85	5.15	L1	4.00	4.30
D	1.85	2.15	L	19.60	20.40
E	1.00	1.40	I	2.30	2.50
F	0.50	0.70	ΦP	3.30	3.70
G1	3.00	3.30			

